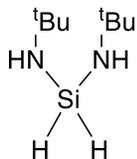


Catalog # 14-1072 Bis(t-butylamino)silane, BTBAS (99.999%-Si) PURATREM



Thermal Behavior:

- Boiling point: 167°C
- Vapor Pressure: ~1.87 Torr/25°C, 6.5 torr/40-45°C [1-2]; Diagram is available in [1]

Technical Notes:

1. ALD low temperature precursor for the silicon oxide and silicon nitride thin film deposition

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
SiO ₂	ALD ^{Therm. Pl.}	50°C	-	O ₃ , P ^l O ₂	250-350°C 50-200°C	3-5
SiN _x	ALD	50°C	-	P ^l N ₂	100-500°C,	6-8

References:

1. *Solid State Technol.*, **2000**, 43, 79.
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4. *J. Phys. Chem. C*, **2016**, 120, 10927
5. *ACS Appl. Mater. Interfaces* **2017**, 9, 42928
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7. *Chem. Mater.* **2016**, 28, 5864
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